

# IRF7854PbF

HEXFET® Power MOSFET

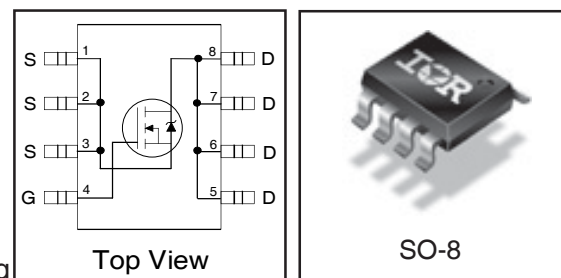
## Applications

- Primary Side Switch in Bridge or two-switch forward topologies using 48V ( $\pm 10\%$ ) or 36V to 60V ETSI range inputs.
- Secondary Side Synchronous Rectification Switch for 12Vout
- Suitable for 48V Non-Isolated Synchronous Buck DC-DC Applications

## Benefits

- Low Gate to Drain Charge to Reduce Switching Losses
- Fully Characterized Capacitance Including Effective  $C_{OSS}$  to Simplify Design, (See App. Note AN1001)
- Fully Characterized Avalanche Voltage and Current

$V_{DSS}$	$R_{DS(on) \text{ max}}$	$I_D$
80V	13.4m $\Omega$ @ $V_{GS} = 10V$	10A



## Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{DS}$	Drain-to-Source Voltage	80	V
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	10	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	7.9	
$I_{DM}$	Pulsed Drain Current ①	79	
$P_D @ T_A = 25^\circ C$	Maximum Power Dissipation	2.5	W
	Linear Derating Factor	0.02	W/ $^\circ C$
dv/dt	Peak Diode Recovery dv/dt ②	11	V/ns
$T_J$	Operating Junction and	-55 to + 150	$^\circ C$
$T_{STG}$	Storage Temperature Range		

## Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead	—	20	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) ③ ⑦	—	50	

Notes ① through ⑦ are on page 8

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### Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	80	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.095	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	11	13.4	m $\Omega$	$V_{GS} = 10V, I_D = 10A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	4.9	V	$V_{DS} = V_{GS}, I_D = 100\mu A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	20	$\mu A$	$V_{DS} = 80V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 80V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$

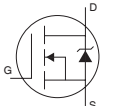
### Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

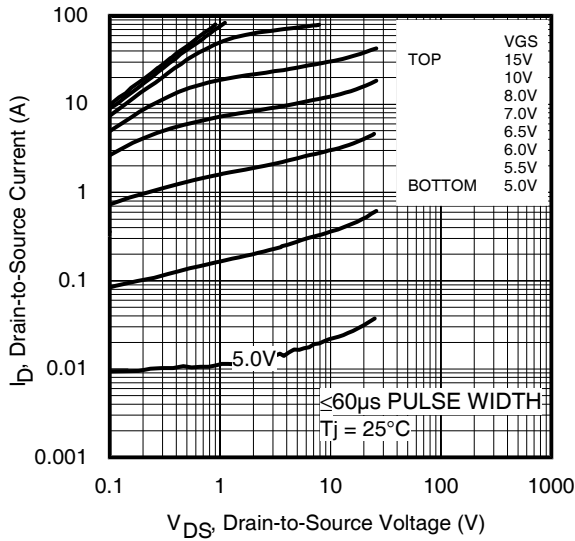
	Parameter	Min.	Typ.	Max.	Units	Conditions	
$g_{fs}$	Forward Transconductance	12	—	—	S	$V_{DS} = 25V, I_D = 6.0A$	
$Q_g$	Total Gate Charge	—	27	41	nC	$I_D = 6.0A$ $V_{DS} = 40V$ $V_{GS} = 10V$ ④	
$Q_{gs}$	Gate-to-Source Charge	—	7.7	—			
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	8.7	—			
$t_{d(on)}$	Turn-On Delay Time	—	9.4	—	ns	$V_{DD} = 40V$ $I_D = 6.0A$ $R_G = 6.2\Omega$ $V_{GS} = 10V$ ④	
$t_r$	Rise Time	—	8.5	—			
$t_{d(off)}$	Turn-Off Delay Time	—	15	—			
$t_f$	Fall Time	—	8.6	—			
$C_{iss}$	Input Capacitance	—	1620	—	pF	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1.0MHz$	
$C_{oss}$	Output Capacitance	—	350	—			
$C_{riss}$	Reverse Transfer Capacitance	—	86	—			
$C_{oss}$	Output Capacitance	—	1730	—			$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0MHz$
$C_{oss}$	Output Capacitance	—	230	—			$V_{GS} = 0V, V_{DS} = 64V, f = 1.0MHz$
$C_{oss\ eff.}$	Effective Output Capacitance	—	410	—			$V_{GS} = 0V, V_{DS} = 0V \text{ to } 64V$ ⑤

### Avalanche Characteristics

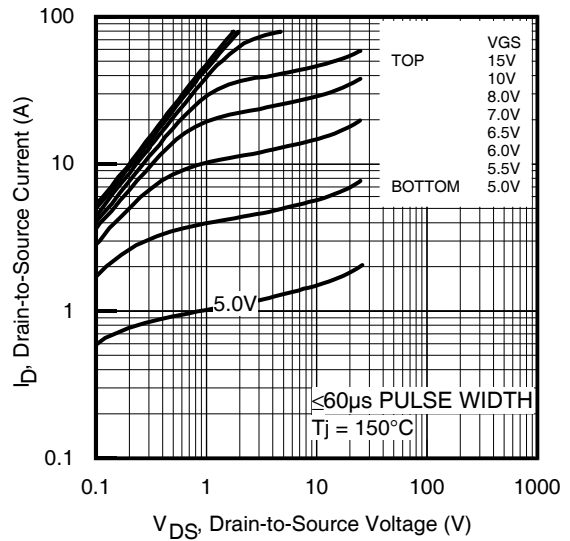
	Parameter	Typ.	Max.	Units
$E_{AS}$	Single Pulse Avalanche Energy ②	—	110	mJ
$I_{AR}$	Avalanche Current ①	—	6.0	A

### Diode Characteristics

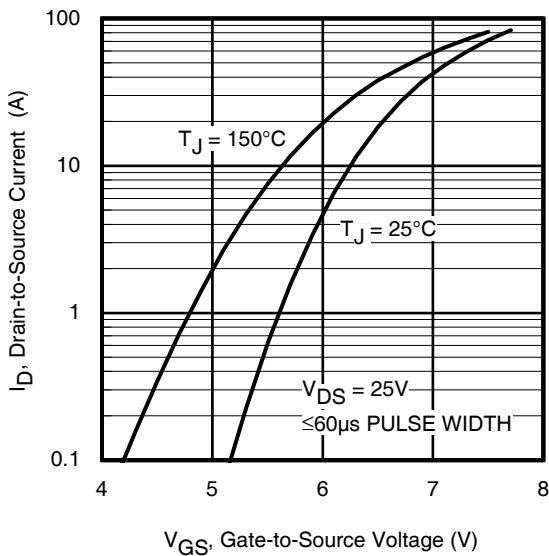
	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	2.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	79		
$V_{SD}$	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 6.0A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	43	65	ns	$T_J = 25^\circ\text{C}, I_F = 6.0A, V_{DD} = 25V$
$Q_{rr}$	Reverse Recovery Charge	—	76	110	nC	$di/dt = 100A/\mu s$ ④
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				



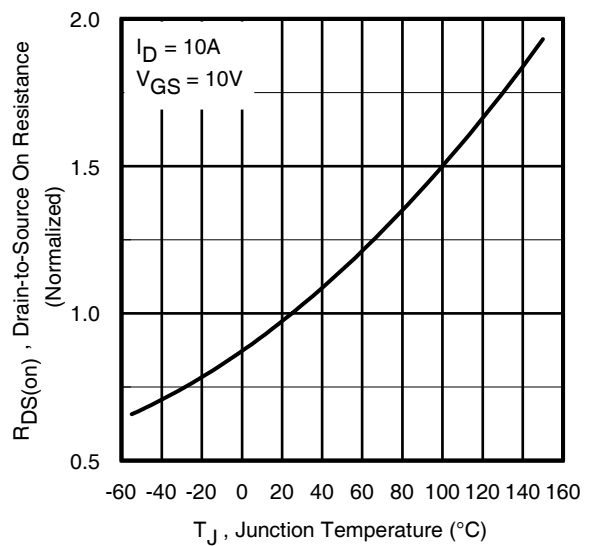
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics

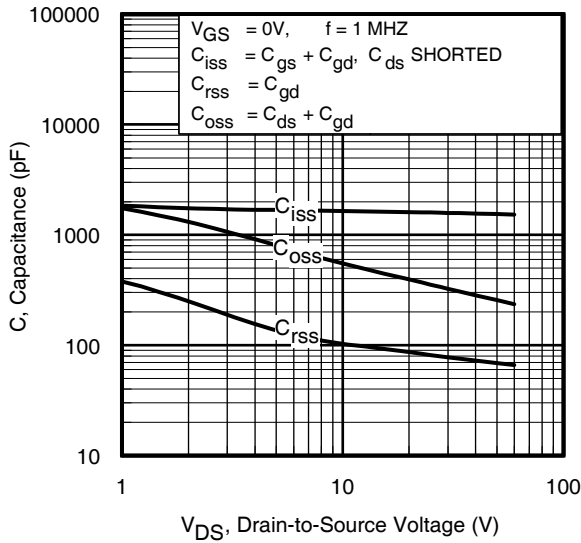


**Fig 3.** Typical Transfer Characteristics

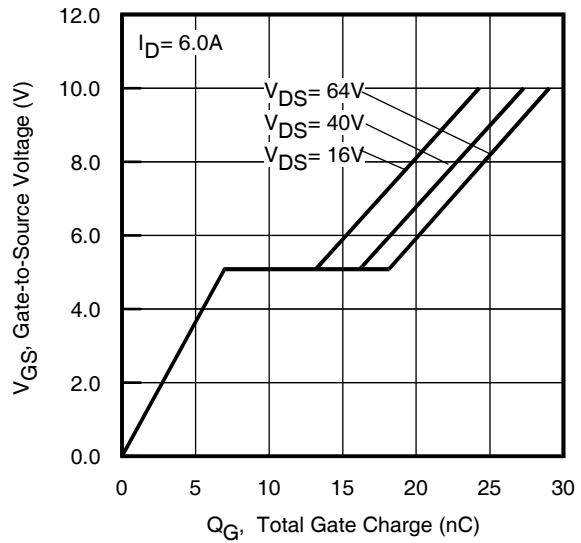


**Fig 4.** Normalized On-Resistance vs. Temperature

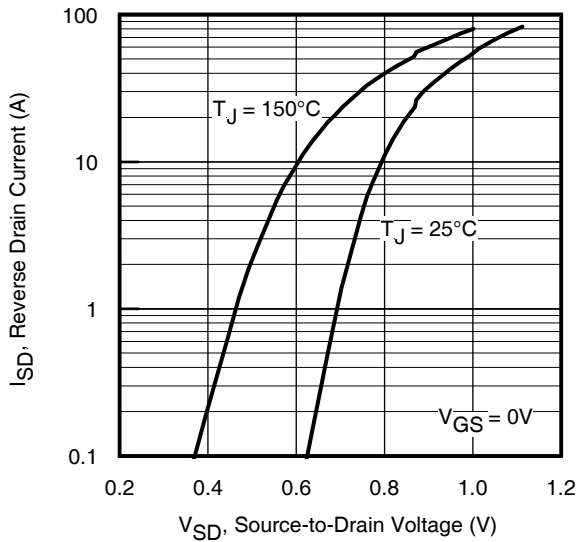
# IRF7854PbF



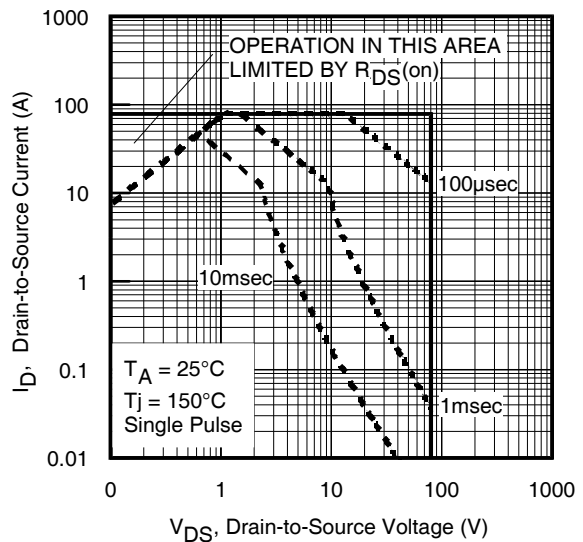
**Fig 5.** Typical Capacitance vs. Drain-to-Source Voltage



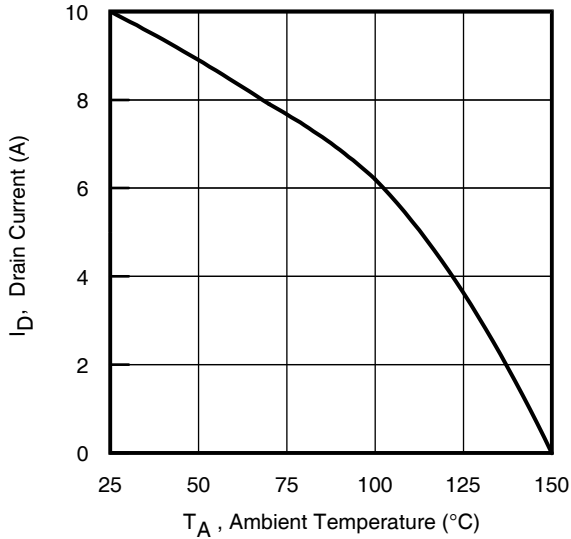
**Fig 6.** Typical Gate Charge vs. Gate-to-Source Voltage



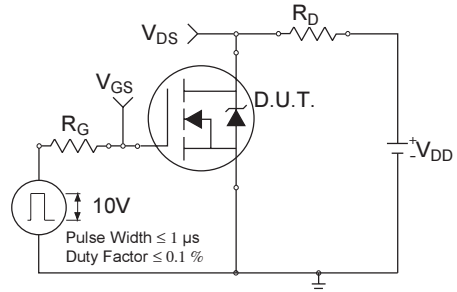
**Fig 7.** Typical Source-Drain Diode Forward Voltage



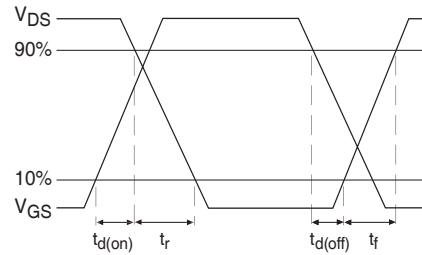
**Fig 8.** Maximum Safe Operating Area



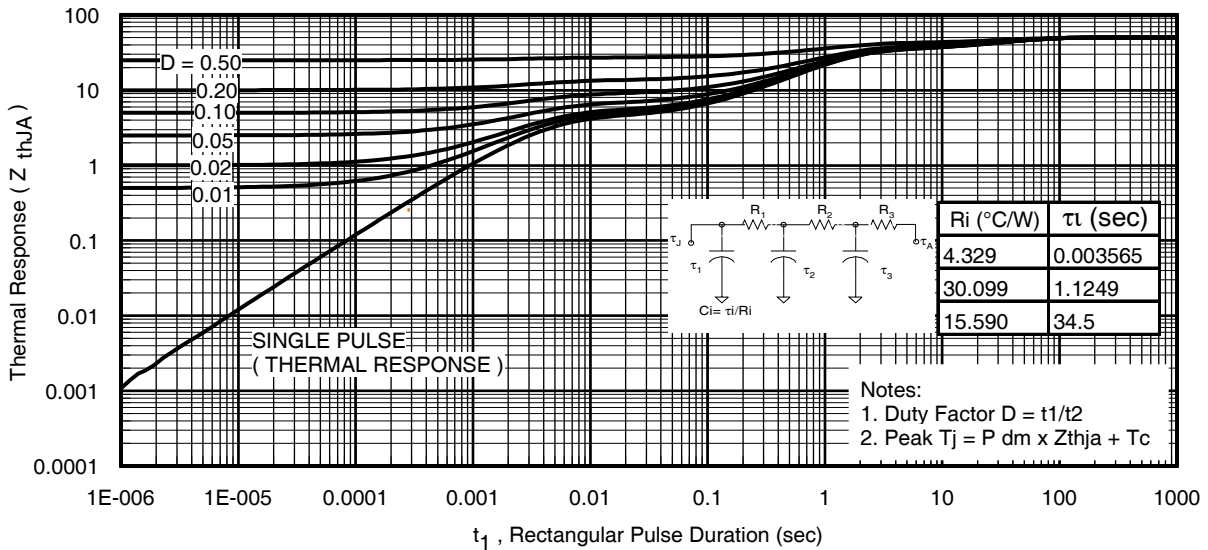
**Fig 9.** Maximum Drain Current vs. Ambient Temperature



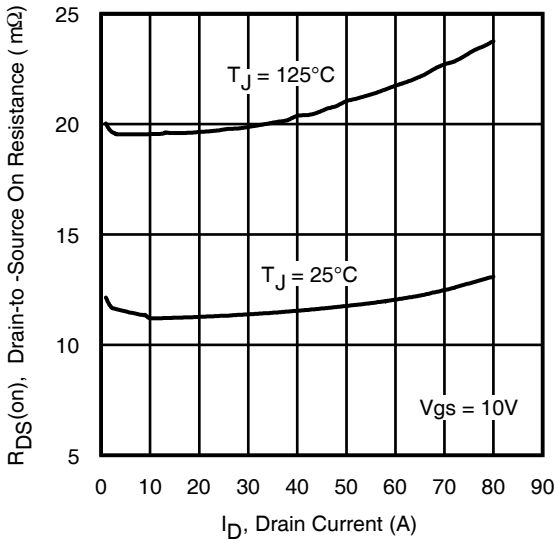
**Fig 10a.** Switching Time Test Circuit



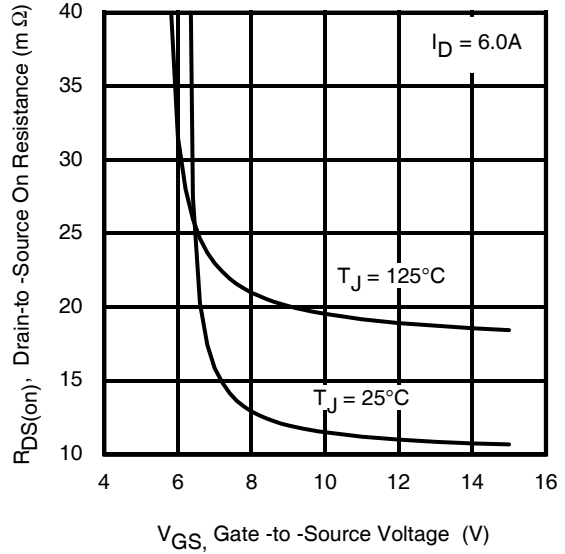
**Fig 10b.** Switching Time Waveforms



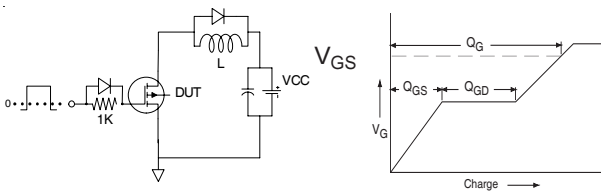
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



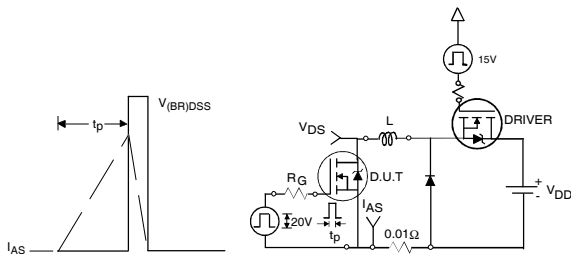
**Fig 12.** On-Resistance vs. Drain Current



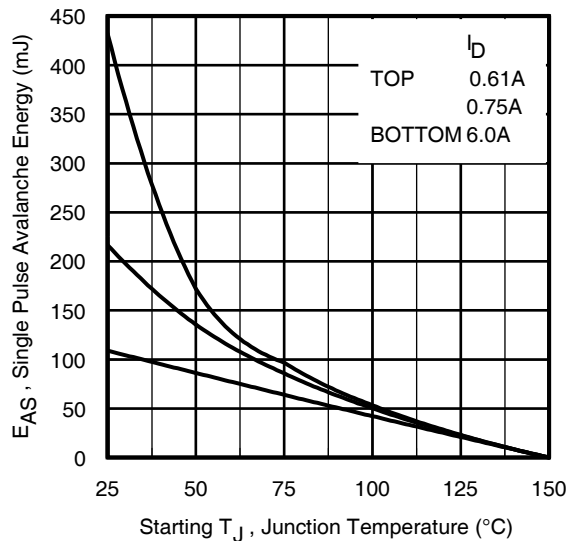
**Fig 13.** On-Resistance vs. Gate Voltage



**Fig 14a&b.** Basic Gate Charge Test Circuit and Waveform



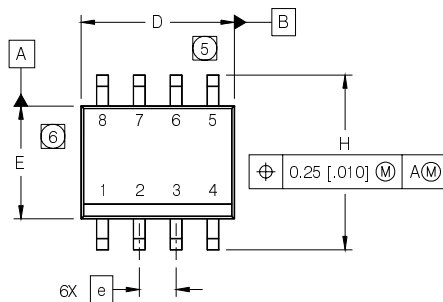
**Fig 15a&b.** Unclamped Inductive Test circuit and Waveforms



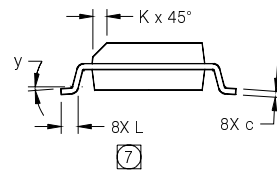
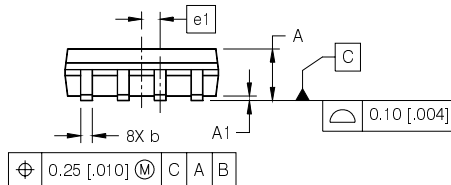
**Fig 15c.** Maximum Avalanche Energy vs. Drain Current

## SO-8 Package Outline

Dimensions are shown in millimeters (inches)



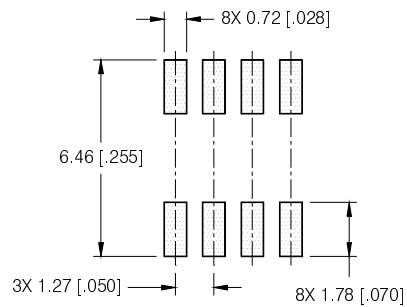
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



**NOTES:**

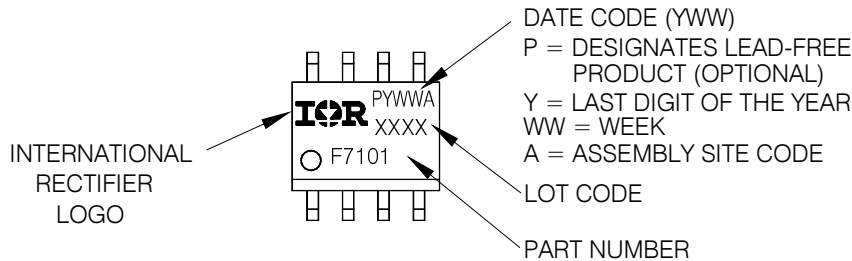
- DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
- CONTROLLING DIMENSION: MILLIMETER
- DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- ⑤** DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [0.006].
- ⑥** DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [0.010].
- ⑦** DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

**FOOTPRINT**



## SO-8 Part Marking Information

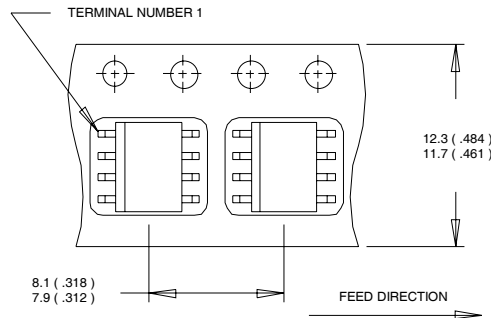
EXAMPLE: THIS IS AN IRF7101 (MOSFET)



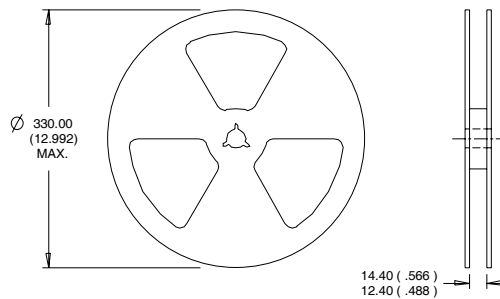
# IRF7854PbF

International  
**IR** Rectifier

## SO-8 Tape and Reel



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
  2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
  3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
  2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 6.0\text{mH}$ ,  $R_G = 25\Omega$ ,  $I_{AS} = 6.0\text{A}$ .
- ③ When mounted on 1 inch square copper board,  $t \leq 10$  sec.
- ④ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ⑤  $C_{OSS}$  eff. is a fixed capacitance that gives the same charging time as  $C_{OSS}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- ⑥  $I_{SD} \leq 6.0\text{A}$ ,  $di/dt \leq 350\text{A}/\mu\text{s}$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_J \leq 150^\circ\text{C}$ .
- ⑦  $R_{\theta}$  is measured at  $T_J$  of approximately  $90^\circ\text{C}$ .

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Industrial market.  
Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

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